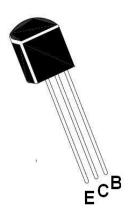




### SILICON PNP EPITAXIAL PLANER TYPE TRANSISTOR



CSB976 TO-92 Plastic Package

### **Applications**

For low-frequency output amplification For DC-DC converter For Stroboscope

#### **Features**

- $\bullet$  Low collector to emitter saturation voltage  $V_{\text{\tiny CE(sat)}}$
- Large collector current I<sub>C</sub>

## Absolute Maximum Ratings (T<sub>a</sub>=25 ° C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to base voltage	V <sub>CBO</sub>	27	V
Collector to emitter voltage	V <sub>CEO</sub>	18	V
Emitter to base voltage	V <sub>EBO</sub>	7	V
Peak collector current	I <sub>CP</sub>	8	Α
Collector current	I <sub>c</sub>	5	Α
Collector power dissipation	P <sub>c</sub>	0.75	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to 150	°C





# Electrical Characteristics (T<sub>a</sub> = 25° C)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = 10V, I_{E} = 0$			100	nA
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = 5V$ , $I_{C} = 0$			1	μΑ
Collector to emitter voltage	V <sub>CEO</sub>	$I_C = 1 \text{mA}, I_B = 0$	18			V
Emitter to base voltage	V <sub>EBO</sub>	$I_{E} = 10 \mu A, I_{C} = 0$	7			V
Forward current transfer ratio	h <sub>FE</sub> <sup>1</sup>	$V_{CE} = 2V, I_{C} = 2A^{2}$	125		625	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{c} = 3A, I_{B} = 0.1A^{2}$		0.4	1	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 6V, I_{E} = 50mA, f = 200MHz$		120		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 20V, I_{E} = 0, f = 1MHz$		60		pF

#### Note

## 1. $\rm h_{\rm FE} \, Rank \, classification$

RANK	Q	R
h <sub>FE</sub>	125 ~ 205	180 ~ 625

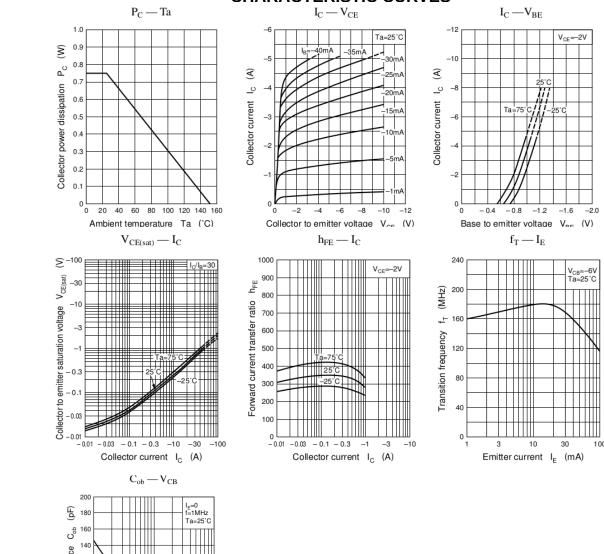
#### 2. Pulse measurement

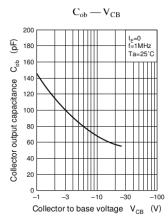


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#### **CHARACTERISTIC CURVES**

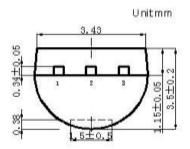


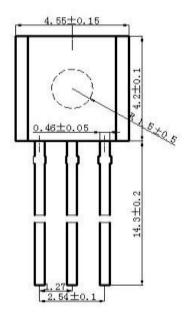






### **TO-92 PACKAGE OUTLINE AND DIMENSIONS**





- 1. EMITTER
- 2. COLLECTOR
- 3. BASE





#### **Customer Notes**

#### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

#### **DISCLAIMER**

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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